

MA2Q705

Silicon epitaxial planar type

For high-frequency rectification

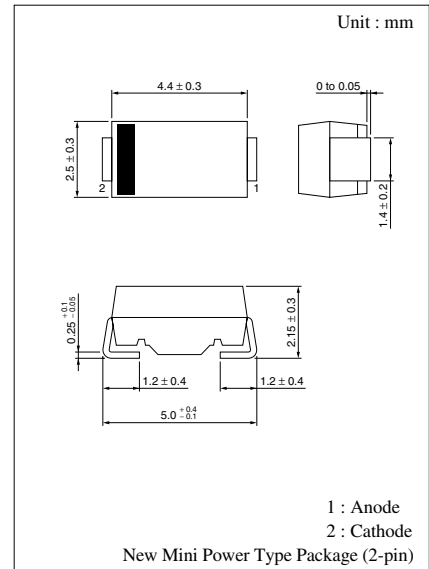
■ Features

- New Mini-power type package (2-pin)
- Allowing to rectify under ($I_{F(AV)} = 1.5 \text{ A}$) condition
- Low V_F (forward voltage) type: $V_F < 0.37 \text{ V}$ (at $I_F = 1.0 \text{ A}$)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	30	V
Repetitive peak reverse voltage	V_{RRM}	30	V
Average forward current	$I_{F(AV)}$	1.5	A
Non-repetitive peak forward surge current*	I_{FSM}	30	A
Junction temperature	T_j	-40 to +125	$^\circ\text{C}$
Storage temperature	T_{stg}	-40 to +125	$^\circ\text{C}$

Note) * : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)



Marking Symbol: PK

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 30 \text{ V}$			3	mA
Forward voltage (DC)	V_F	$I_F = 1.0 \text{ A}$			0.37	V
Terminal capacitance	C_t	$V_R = 10 \text{ V}, f = 1 \text{ MHz}$		90		pF
Reverse recovery time* ^{1,2}	t_{rr}	$I_F = I_R = 100 \text{ mA}$ $I_{rr} = 0.1 \cdot I_R, R_L = 100 \Omega$			50	ns

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

2. Rated input/output frequency: 20 MHz

3. *1 : Obtained by fixing the element to the printed-circuit board (glass epoxy)

*2 : t_{rr} measuring circuit

